

Supporting Information

Article

Dual-Functional Nanoscale Devices Using Phase-Change Materials: A Reconfigurable Perfect Absorber with Nonvolatile Resistance-Change Memory Characteristics

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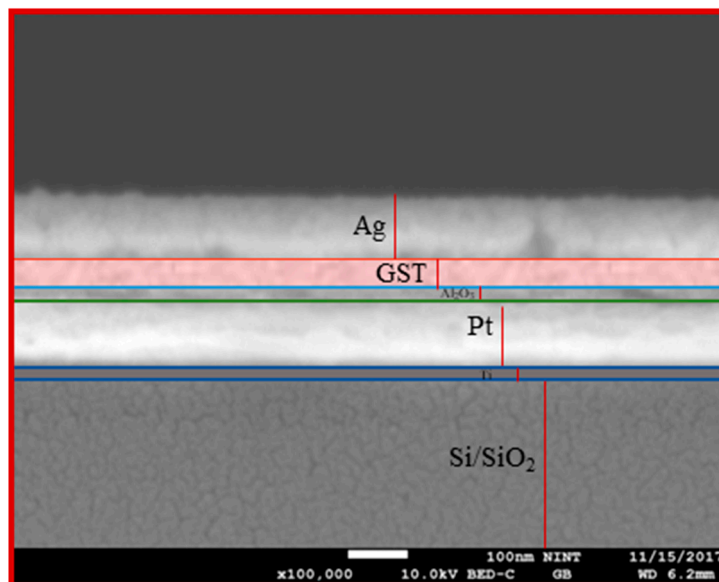
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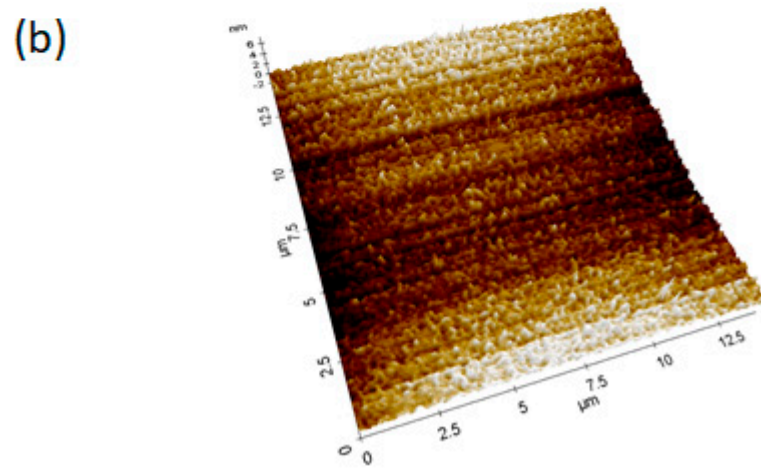
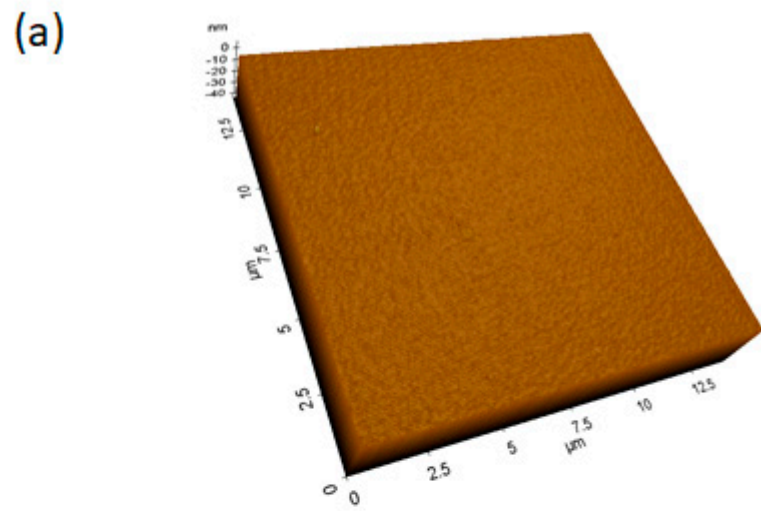
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Supporting Figure S1. A SEM cross section of the fabricated device illustrates the successfully fabricated MPA.



Supporting Figure S2. (a) A surface morphology of the GST thin film at (a) amorphous and (b) crystalline state.